

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of performing a chemical vapor deposition process comprising:

cleaning a process chamber at a first chamber pressure by introducing a cleaning gas into the process chamber through a cleaning gas supply line;
loading a wafer into the process chamber after said cleaning; and
depositing a film on the wafer at a second chamber pressure lower than the first chamber pressure by introducing a deposition gas into the process chamber, while preventing wherein during said depositing, a back flow preventing gas is introduced into the process chamber through the cleaning gas supply line to prevent the deposition gas from flowing back toward the cleaning gas supply line.

2. (Canceled).

3. (Currently Amended) The method as claimed in claim 21, wherein the back-flow preventing gas is at least any one selected from a group consisting of nitrogen, argon and helium.

4. (Currently Amended) The method as claimed in claim 21, wherein a flow rate of the back-flow preventing gas is at a ratio of 30 to 100 % with respect to a flow rate of the deposition gas.

5. (Original) The method as claimed in claim 1, wherein the cleaning gas is a

gas including a fluorine radical which is generated by exciting NF₃ gas at an exterior of the process chamber before said cleaning.

6. (Original) The method as claimed in claim 1, wherein the cleaning gas includes an active gas and an inert gas as a carrier gas for carrying the active gas.

7. (Original) The method as claimed in claim 6, wherein the inert gas is at least any one selected from a group consisting of nitrogen, argon and helium.

8. (Original) The method as claimed in claim 6, wherein the back-flow preventing gas is introduced into the process chamber through the cleaning gas supply line to prevent the deposition gas from flowing back toward the cleaning gas supply line, the carrier gas being the same as the back-flow preventing gas and being supplied from a same source.

9. (Original) The method as claimed in claim 6, wherein the back-flow preventing gas is introduced into the process chamber through the cleaning gas supply line to prevent the deposition gas from flowing back toward the cleaning gas supply line, the carrier gas being different from the back-flow preventing gas and being supplied separately from a gas source that is different than a back-flow preventing gas source.

Claims 10-20. (Canceled)

21. (New) The method as claimed in claim 1, wherein the first chamber pressure is 400 to 550Torr.

22. (New) The method as claimed in claim 21, wherein the second chamber pressure is 170 to 230Torr.

23. (New) The method as claimed in claim 1, wherein before introducing the deposition gas into the process chamber, the deposition gas is mixed outside of the chamber.

24. (New) A method of performing a chemical vapor deposition processing comprising:

cleaning a process chamber at a first chamber pressure by producing a cleaning gas into the process chamber through a cleaning gas supply line;

pre-coating a film on inner sidewall of the process chamber at a chamber pressure lower than the first chamber pressure by introducing a deposition gas into the process chamber, wherein during said pre-coating, a back flow preventing gas is introduced into the process chamber through the cleaning gas supply line to prevent the deposition gas from flowing back toward the cleaning gas supply line;

loading a wafer into the process chamber after said the cleaning; and

depositing a film on the wafer at a chamber pressure lower than the first chamber pressure by introducing a deposition gas into the process chamber, wherein during said depositing, a back flow preventing gas is introduced into the process chamber through the cleaning gas supply line to prevent the deposition gas from flowing back toward the cleaning gas supply line.